

- ⚡ L3: (1) 10/225715
- ⚡ L4: (2) "8660880".pn.
- ⚡ L5: (10191) {dielectric adj|constant relative adj|permittivity\$3 permittivity\$3}
- ⚡ L6: (4779) high adj k
- ⚡ L7: (26128) high near L5
- ⚡ L8: (29294) L8 I7
- ⚡ L9: (10542) [charge near3 {strap\$4 trap\$4 nitride}]
- ⚡ L10: (21495) oxynitride
- ⚡ L11: (163906) tunnel\$4
- ⚡ L12: (48180) L8 L10
- ⚡ L13: (436) L11 near9 L12
- ⚡ L14: (189) L9 near9 L12
- ⚡ L15: (32) L18 and L14
- ⚡ L16: (2) "6461848".pn.
- ⚡ L17: (94) 15 16
- ⚡ L18: (4) "6594385".pn. "6649925".pn.
- ⚡ L19: (1157) {ALD AL atomic adj|layer adj|{deposition epitaxial\$4 epitaxyl}}
- ⚡ L20: (2) 18 and 19
- ⚡ L21: (38) 15 16 18
- ⚡ L22: (10) 21 and 19
- ⚡ L23: (20812) lanthanide
- ⚡ L25: (0118) adj|18 anf|18
- ⚡ L24: (28) 18 anf|18
- ⚡ L26: (2) backward citation search 1
- ⚡ L27: (8) Backward citation search 1

05/2005

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2			Kim, Yeong	US 6395240 B1	2002	12 Capacitor for a semiconductor device	498/25	257/E21.0		P				US 6395240 B1
3			Park, In-se	US 6144080 A	2000	2 Integrated circuit devices having buffe	257/81	257/298		P				US 6144080 A
4			Gardner, M	US 6124620 A	2000	17 Incorporating barrier atoms into a gat	257/411	257/348		P				US 6124620 A
5			Dautartas, US	6124158 A	2000	6 Method of reducing carbon contamina	438/21	257/E21.19		P				US 6124158 A
6			Chen, Robe	US 5763922 A	1998	15 CMOS integrated circuit having PMOS a	257/371	257/411		P				US 5763922 A
7			Roeber, Jeff	US 5719477 A	1998	15 Ferroelectric integrated circuit structu	257/29	257/761		P				US 5719477 A
8			Wallace, Ro	US 5319793 A	1994	6 Directed effusive beam atomic layer e	427/24	118/50		P				US 5319793 A